

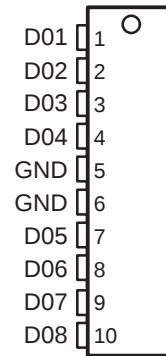
- Designed to Reduce Reflection Noise
- Repetitive Peak Forward Current 300 mA
- 8-Bit Array Structure Suited for Bus-Oriented Systems

description

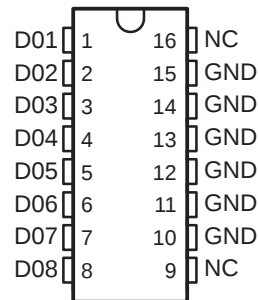
This Schottky barrier diode bus-termination array is designed to reduce reflection noise on memory bus lines. This device consists of an 8-bit high-speed Schottky diode array suitable for a clamp to GND.

The SN74S1056 is characterized for operation from 0°C to 70°C.

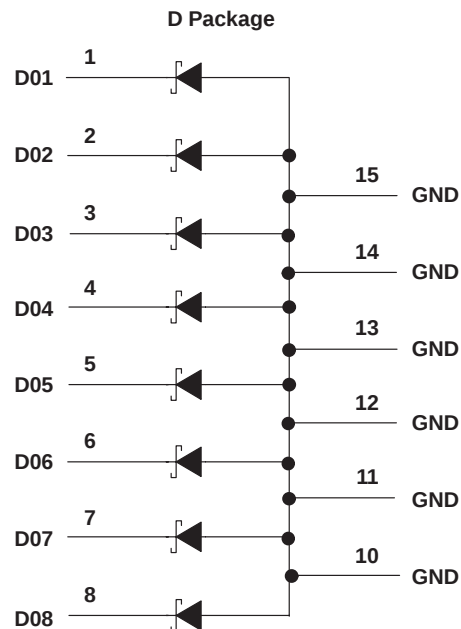
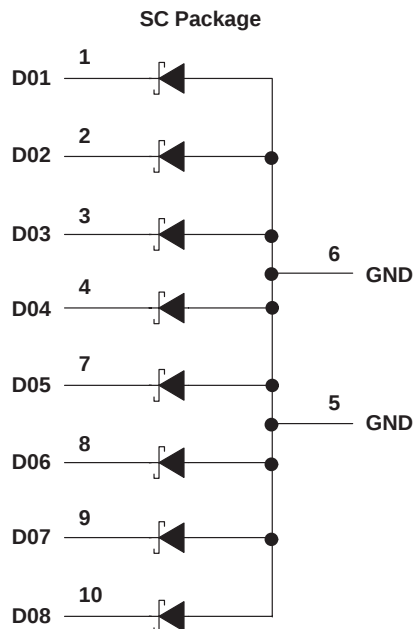
SC PACKAGE
(TOP VIEW)



D PACKAGE
(TOP VIEW)



schematic diagrams



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

TEXAS
INSTRUMENTS

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SN74S1056

8-BIT SCHOTTKY BARRIER DIODE

BUS-TERMINATION ARRAY

SDLS019B – APRIL 1990 – REVISED JULY 1997

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Steady-state reverse voltage, V_R	7 V
Continuous forward current, I_F : Any D terminal from GND	50 mA
Total through all GND terminals	170 mA
Repetitive peak forward current, I_{FRM} (see Note 1): Any D terminal from GND	300 mA
Total through all GND terminals	1.2 A
Continuous total power dissipation at (or below) 25°C free-air temperature	1000 mW
Operating free-air temperature range	0°C to 70°C
Storage temperature range, T_{stg}	–65°C to 150°C

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: These values apply for $t_W \leq 100 \mu s$, duty cycle $\leq 20\%$.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

single-diode operation (see Note 2)

PARAMETER	TEST CONDITIONS	MIN	TYP [‡]	MAX	UNIT
I_R Static reverse current	$V_R = 7 V$			10	μA
V_F Static forward voltage	$I_F = 18 mA$		0.65	0.85	V
	$I_F = 50 mA$		0.8	1	
V_{FM} Peak forward voltage	$I_F = 300 mA$		1.41		V
C_t Total capacitance	$V_R = 0 V$, $f = 1 MHz$		11	20	pF
	$V_R = 2 V$, $f = 1 MHz$		8	16	

[‡] All typical values are at $T_A = 25^\circ C$.

NOTE 2: Test conditions and limits apply separately to each of the diodes. The diodes not under test are open-circuited during the measurement of these characteristics.

multiple-diode operation

PARAMETER	TEST CONDITIONS	MIN	TYP [‡]	MAX	UNIT
I_X Internal crosstalk current	Total I_F current = 1.2 A, See Note 3		0.6	2	mA
	Total I_F current = 126 mA, See Note 3		0.01	0.1	

[‡] All typical values are at $T_A = 25^\circ C$.

NOTE 3: I_X is measured under the following conditions with one diode static, all others switching:

Switching diodes: $t_W = 100 \mu s$, duty cycle = 20%

Static diode: $V_R = 5 V$

The static diode input current is the internal crosstalk current I_X .

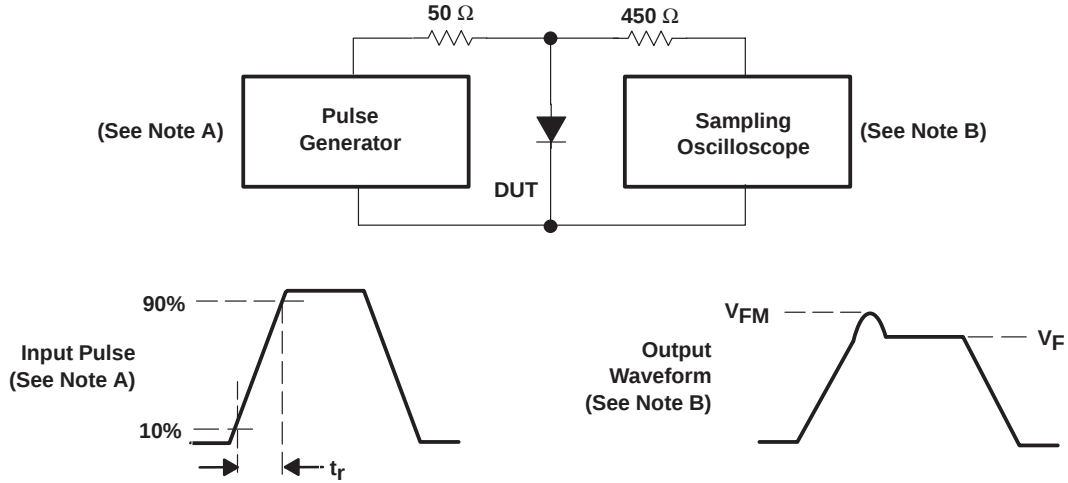
switching characteristics, $T_A = 25^\circ C$ (see Figures 1 and 2)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{rr} Reverse recovery time	$I_F = 10 mA$, $I_{RM(REC)} = 10 mA$, $I_{R(REC)} = 1 mA$, $R_L = 100 \Omega$		5	10	ns



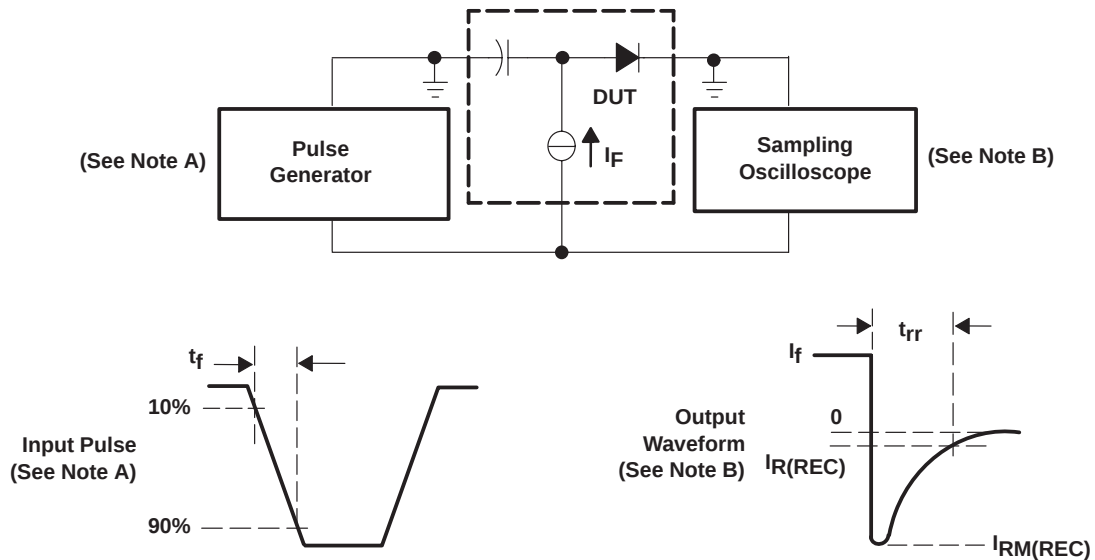
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PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The input pulse is supplied by a pulse generator having the following characteristics: $t_r = 20$ ns, $Z_O = 50$ Ω, freq = 500 Hz, duty cycle = 0.01.
 B. The output waveform is monitored by an oscilloscope having the following characteristics: $t_r \leq 350$ ps, $R_i = 50$ Ω, $C_i \leq 5$ pF.

Figure 1. Forward Recovery Voltage



- NOTES: A. The input pulse is supplied by a pulse generator having the following characteristics: $t_f = 0.5$ ns, $Z_O = 50$ Ω, $t_W \geq 50$ ns, duty cycle = 0.01.
 B. The output waveform is monitored by an oscilloscope having the following characteristics: $t_r \leq 350$ ps, $R_i = 50$ Ω, $C_i \leq 5$ pF.

Figure 2. Reverse Recovery Time

SN74S1056

8-BIT SCHOTTKY BARRIER DIODE

BUS-TERMINATION ARRAY

SDLS019B – APRIL 1990 – REVISED JULY 1997

APPLICATION INFORMATION

Large negative transients occurring at the inputs of memory devices (DRAMs, SRAMs, EPROMs, etc.) or on the CLOCK lines of many clocked devices can result in improper operation of the devices. The SN74S1056 diode termination array helps suppress negative transients caused by transmission-line reflections, crosstalk, and switching noise.

Diode terminations have several advantages when compared to resistor termination schemes. Split resistor or Thevenin equivalent termination can cause a substantial increase in power consumption. The use of a single resistor to ground to terminate a line usually results in degradation of the output high level, resulting in reduced noise immunity. Series damping resistors placed on the outputs of the driver reduce negative transients, but they also can increase propagation delays down the line, as a series resistor reduces the output drive capability of the driving device. Diode terminations have none of these drawbacks.

The operation of the diode arrays in reducing negative transients is explained in the following figures. The diode conducts current when the voltage reaches a negative value large enough for the diode to turn on. Suppression of negative transients is tracked by the current-voltage characteristic curve for that diode. A typical current versus voltage plot for the SN74S1056 is shown in Figure 3.

To illustrate how the diode arrays act to reduce negative transients at the end of a transmission line, the test setup in Figure 4(a) was evaluated. The resulting waveforms with and without the diode are shown in Figure 4(b).

The maximum effectiveness of the diode arrays in suppressing negative transients occurs when the diode arrays are placed at the end of a line and/or the end of a long stub branching off a main transmission line. The diodes also can be used to reduce the negative transients that occur due to discontinuities in the middle of a line. An example of this is a slot in a backplane that is provided for an add-on card.

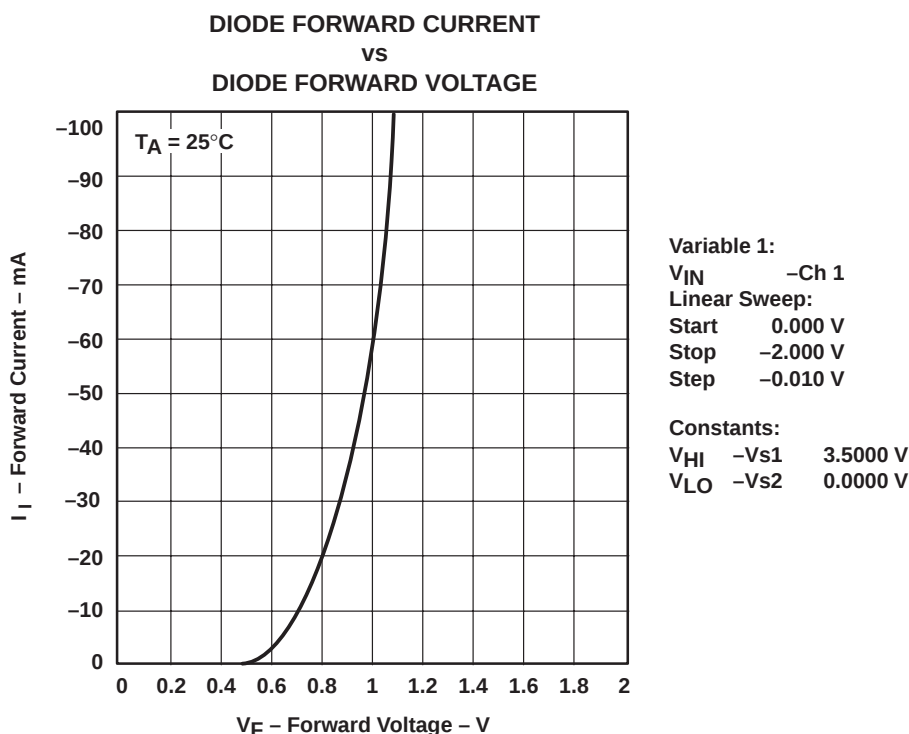


Figure 3. Current Versus Voltage for the SN74S1056

$Z_0 = 50 \, \Omega$
Length = 36 in.

The diagram shows a transmission line circuit. On the left, an AC voltage source is connected to the input of a transmission line, represented by a cylinder. Above the cylinder, the characteristic impedance is given as $Z_0 = 50 \, \Omega$ and the length is given as 36 in. The output of the transmission line is connected to a switch and a load, represented by a diode symbol, which is then connected to ground.

31.500 ns 56.500 ns 81.500 ns

End-of-Line Without Diode

End-of-Line With Diode

Vmarker 1

Vmarker 2

Ch 1 = 1.880 V/div

Timebase = 5.00 ns/V

Memory 1 = 1.880 V/div

Vmarker 1 = -1.353 V

Vmarker 2 = -3.647 V

Offset = 0.000 V

Delay = 56.500 ns

Delta V = -2.293 V

Figure 4. Diode Test Setup and Oscilloscope Display

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